

L Number	Hits	Search Text	DB	Tim stamp
-	1	passivati n.clm. and (p rous near5 (s mic nduct r adj lay r)).clm.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/01/28 16:09
-	1	passivation.clm. and (porous near5 (semiconductor adj layer))	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/01/28 16:09
-	23	passivation and (porous near5 (semiconductor adj layer))	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/01/28 16:09
-	4	passivation and (porous near5 (semiconductor adj layer)) and (tft or (thin near film near transistor))	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/01/28 16:11
-	2	passivation and (porous near2 (semiconductor adj layer)) and (tft or (thin near film near transistor))	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/01/28 16:11
-	20	passivation and (porous near2 (semiconductor adj layer))	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/01/28 16:11
-	10	passivation and (porous near2 (semiconductor adj layer)).clm.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/01/28 16:12
-	103	(porous near2 (semiconductor adj layer)).clm.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/01/28 16:12
-	3	(porous near2 (semiconductor adj layer)).clm. and (tft or (thin near film near transistor)).clm.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/01/28 16:13
-	3	(p r us near2 (semic ndu tor adj lay r)).clm. and (tft or (thin near film near transist r)).clm. and matrix	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/01/28 16:13

-	1	(porous near2 (semiconductor adj layer)). Im. and (tft or (thin near film near transistor)). Im. and matrix. Im.	USPAT; US-P PUB; EPO; JPO; DERWENT; IBM_TDB	2004/01/28 16:13
-	3	(porous near2 (semiconductor adj layer)).clm. and (tft or (thin near film near transistor)).clm. and matrix	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/01/28 16:13
-	3	(porous near2 (semiconductor adj layer)).clm. and (tft or (thin near film near transistor)).clm. and (active near matrix)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/01/28 16:14
-	4	(porous near2 (semiconductor adj layer)).clm. and (tft or (thin near film near transistor)) and (active near matrix)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/01/28 16:14
-	9	(porous near2 (semiconductor adj layer)) and (tft or (thin near film near transistor)) and (active near matrix)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/01/28 16:14
-	2	(porous near2 (semiconductor adj layer)) and (tft or (thin near film near transistor)) and (active near matrix) and passivation	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/01/28 16:14
-	4	(porous near5 (semiconductor adj layer)) and (tft or (thin near film near transistor)) and (active near matrix) and passivation	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/01/28 16:14